

(54) Title of the invention : DIODE LIGHTING ARRANGEMENT

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(57) Abstract :

22The invention describes a diode lighting arrangement(1A 1B 1C) comprising a light emitting diode arrangement (1 2) comprising at least two exposed serially connected light emitting diodes (1) connected in parallel with an electrostatic discharge protection diode arrangement (2); and an electrostatic discharge diverting arrangement (4 50) extending in physical proximity to an interconnect (10) between adjacent light emitting diodes (1) which diverting arrangement (4 50) is realised to divert electrostatic discharge (S) from the interconnect (10) to a region of low potential (21 22 GND). The invention further describes an automotive lighting assembly (3A 3B) comprising such a diode lighting arrangement (1A 1B 1C). The invention also describes a method of manufacturing a diode lighting arrangement (1A 1B 1C) which method comprises the steps of serially connecting a light emitting diode arrangement (1 2) comprising at least two exposed serially connected light emitting diodes (1) in parallel with an electrostatic discharge protection diode arrangement (2); and arranging an electrostatic discharge diverting arrangement (4 50 60) to extend in physical proximity to at least one interconnect (10) between adjacent light emitting diodes (1) which diverting arrangement (4 50) is realised to divert electrostatic discharge (S) from the interconnect (10) to a region of low potential (21 22 GND).

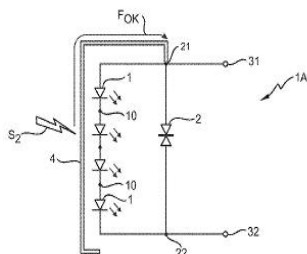


Fig. 2

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